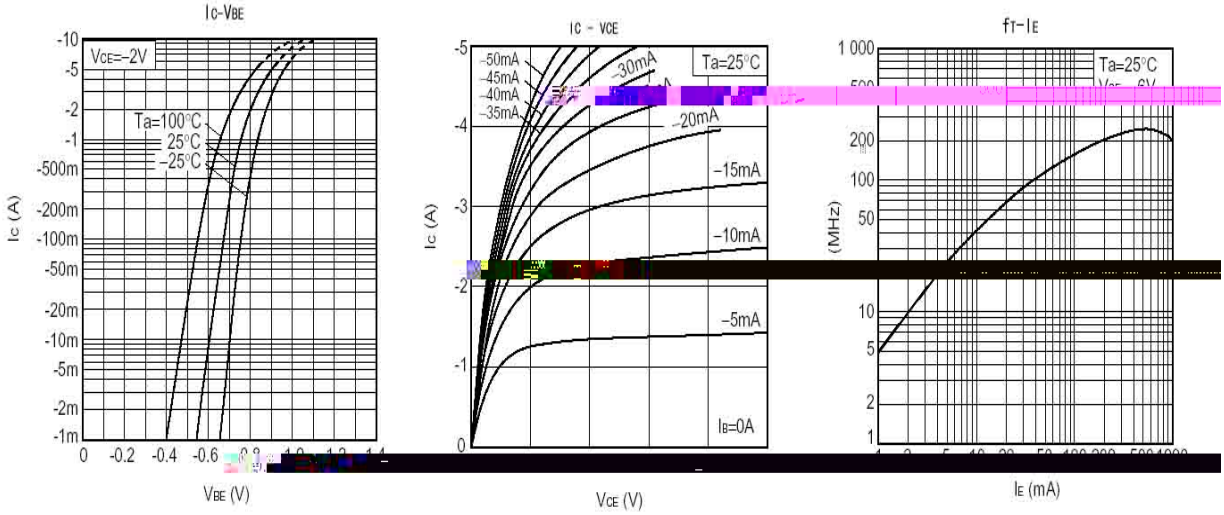
/ Absolute Maximum Ratings(Ta=25)

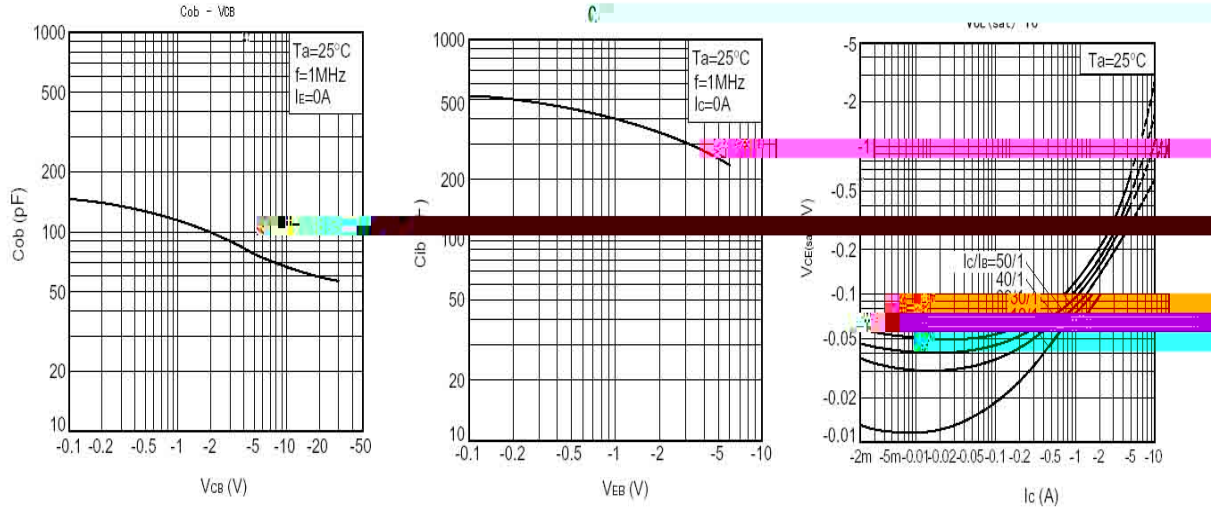
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current-Continuous	I_C	-5.0	A
Collector Base-Continuous(Pulse)	I_{CP}	-10	A
Collector Power Dissipation	P_C	0.5	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-50μA I_E=0	-30			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-20			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-50μA I_C=0	-6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-20V I_E=0			-0.5	μA
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=-5.0V I_C=0			-0.5	μA
DC Current Gain	h_{FE}	V_{CE}=-2.0V I_C=-0.5A	82		390	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-4.0A I_B=-0.1A		-0.35	-1.0	V
Transition Frequency	f_T	V_{CE}=-6.0V I_C=-50mA f=30MHz		120		MHz
Collector Output Capacitance	C_{ob}	V_{CE}=-20V I_E=0 f=1.0MHz		60		pF

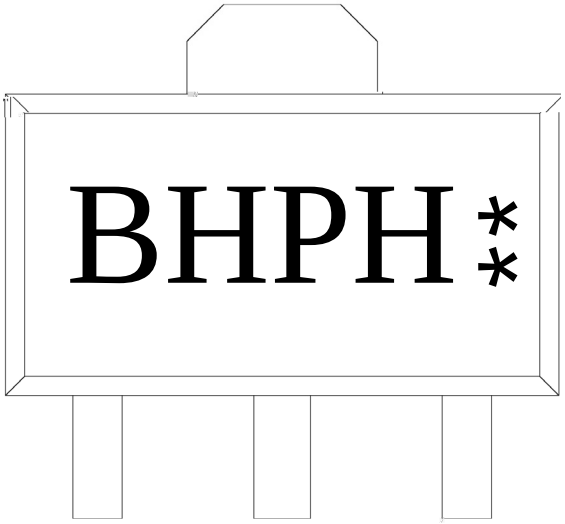
/ Electrical Characteristic Curve







/ Marking Instructions



BH

P h_{FE}

H

**

Note:

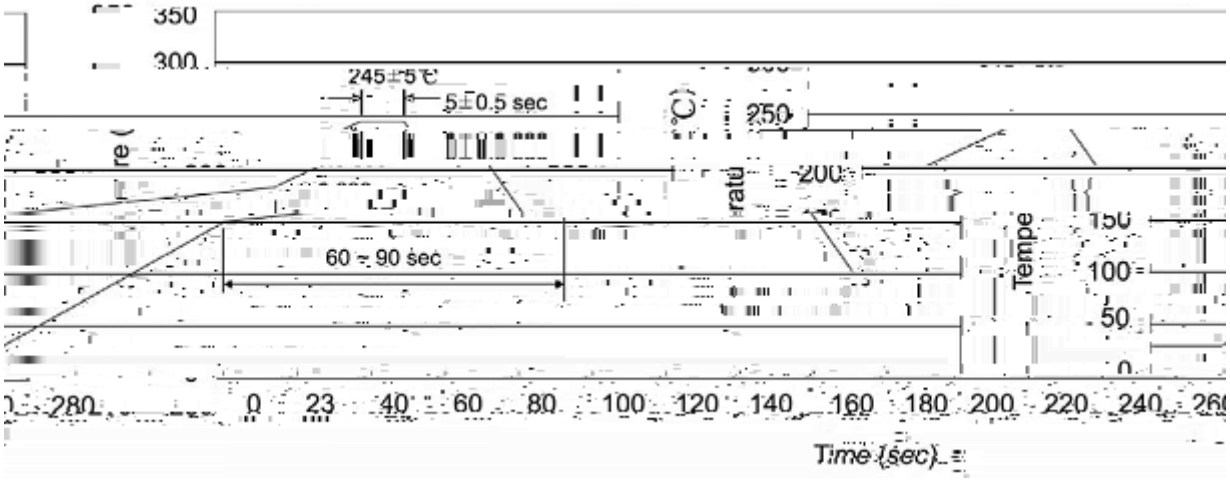
BH: Product Type.

P h_{FE} Classifications Symbol

H: Company Code.

**: Lot No. Code, code change with Lot No.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



1	25	150	60	90sec;	
2	245±5			5±0.5sec;	
3		2	10	/sec.	

Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3.